

IN THE SPECIFICATION:

Please amend Paragraph [0072] to read as follows:

[0072] The separation grooves 30 are made so as to reach the non-doped GaN substrate 10, and a Si._{sub.3}N._{sub.4} membrane 28 as an insulating film covers a surface of the separation grooves 30. On the shelf shaped n-GaN clad layer 22, n-electrodes 27 made of Ti/Au are formed at the boundary between the light emitting element 20 and the separation grooves 30. The bridge wiring 40 made of Ti/Pt/Au connects the n-electrodes 27 to the n-electrodes p-electrodes 26 on the light emitting element 20 that is next to the n-electrodes 27, in one-to-one relation.